

Electronic structure of solid matter

MSc course 2019

Problem set 2

Exercise 1

Considering a system of independent electrons the expectation value of a Hermitean operator \mathcal{A} is given by

$$A = \sum_n f(\varepsilon_n) \langle \varphi_n | \mathcal{A} | \varphi_n \rangle , \quad (1)$$

where $f(\varepsilon) = 1/(1 + e^{(\varepsilon - \mu)/k_B T})$ is the Fermi distribution, μ is the chemical potential, and $|\varphi_n\rangle$ are the eigenfunctions of the one-electron Hamiltonian,

$$\mathcal{H} |\varphi_n\rangle = \varepsilon_n |\varphi_n\rangle . \quad (2)$$

Prove that A can be expressed as

$$A = -\frac{1}{\pi} \operatorname{Im} \int_{\mathcal{C}} dz f(z) \operatorname{Tr}(\mathcal{A} \mathcal{G}(z)) - 2k_B T \sum_{\operatorname{Im} z_k > 0} \operatorname{Re} \operatorname{Tr}(\mathcal{A} \mathcal{G}(z_k)) , \quad (3)$$

where $\mathcal{G}(z) = (z - \mathcal{H})^{-1}$ is the resolvent operator, \mathcal{C} denotes a contour in the upper complex semiplane with the endpoints $-\infty$ and ∞ , and $z_k = \mu + i(2k + 1)\pi k_B T$ ($k \in \mathbb{Z}$) are the poles of $f(z)$ (fermionic Matsubara poles) lying between the real axis and \mathcal{C} .

Exercise 2

Let the tight-binding Hamiltonian matrix $\underline{H} = \{\underline{H}_{ij}\}$ describe the electrons in a solid. The atom at a given site n is replaced by an other atom, characterized by the on-site matrix, \underline{H}'_n , while the off-site blocks of the Hamiltonian are supposed to be unchanged.

(a) Prove that the site-diagonal block of the resolvent matrix related to site n is

$$\underline{G}'^{nn}(z) = \underline{G}^{nn}(z) (\underline{I} - \Delta \underline{H}_n \underline{G}^{nn}(z))^{-1} , \quad (4)$$

where $\Delta \underline{H}_n = \underline{H}'_n - \underline{H}_n$ and $\underline{G}^{nn}(z)$ is the site-diagonal block of the resolvent matrix of the host system.

(b) Show that in case of a disordered binary alloy the single-site CPA condition for the t -matrices is equivalent with the following condition for the resolvent matrices,

$$\underline{G}_c^{mn}(z) = c \underline{G}_A^{mn}(z) + (1 - c) \underline{G}_B^{mn}(z) , \quad (5)$$

where $\underline{G}_\alpha^{mn}(z)$ denotes the site-diagonal block of the resolvent matrix when a single impurity of type $\alpha \in \{A, B\}$ is embedded into the effective medium at site n . (*This exercise was in fact discussed in the course.*)

Exercise 3

Consider the case when two atoms at sites n and m are replaced in Exercise 2. Prove that the corresponding site-off-diagonal block of the resolvent matrix can be expressed as

$$\underline{G}^{nm} = \tilde{\underline{D}}_n (\underline{I} - \underline{G}^{nm} \underline{t}_m \underline{G}^{mn} \underline{t}_n)^{-1} \underline{G}^{nm} \underline{D}_m, \quad (6)$$

where

$$\underline{D}_m = (\underline{I} - \Delta \underline{H}_m \underline{G}^{mm})^{-1}, \quad \tilde{\underline{D}}_n = (\underline{I} - \underline{G}^{nn} \Delta \underline{H}_n)^{-1}, \quad \underline{t}_n = \Delta \underline{H}_n \tilde{\underline{D}}_n = \underline{D}_m \Delta \underline{H}_m !$$

Exercise 4

The nearest neighbor tight-binding Hamiltonian for a single-band system on a simple one-dimensional lattice is given by

$$H_{ij} = \varepsilon_0 \delta_{ij} + V (\delta_{i,j+1} + \delta_{i,j-1}), \quad (7)$$

where i and j denote sites of the lattice ($V > 0$). Prove that, for $\text{Im } z > 0$ and $\varepsilon_0 - 2V < \varepsilon \equiv \text{Re } z < \varepsilon_0 + 2V$, the resolvent matrix can be expressed as

$$G^{ij}(z) = \frac{\left(\frac{z-\varepsilon_0}{2V} - \sqrt{\left(\frac{z-\varepsilon_0}{2V} \right)^2 - 1} \right)^{|i-j|}}{2V \sqrt{\left(\frac{z-\varepsilon_0}{2V} \right)^2 - 1}}, \quad (8)$$

consequently,

$$G^{ii}(z) = \frac{1}{\sqrt{(z - \varepsilon_0)^2 - 4V^2}}, \quad (9)$$

and the density of states per lattice site is

$$n(\varepsilon) = \frac{1}{\pi \sqrt{4V^2 - (\varepsilon - \varepsilon_0)^2}} ! \quad (10)$$

Exercise 5

Show that the single-site CPA condition for the above mentioned system can be written in the form,

$$\varepsilon_c = c\varepsilon_A + (1-c)\varepsilon_B - (\varepsilon_A - \varepsilon_c(z))(\varepsilon_B - \varepsilon_c(z))G_c^{00}(z), \quad (11)$$

where c is the concentration of component A , ε_A and ε_B are the on-site energies for components A and B , $\varepsilon_c(z)$ is the self-energy for the effective medium and

$$G_c^{00}(z) = \frac{1}{\sqrt{(z - \varepsilon_c(z))^2 - 4V^2}} ! \quad (12)$$

Exercise 6

Let us fix the on-site energies in the above example as

$$\varepsilon_A = \varepsilon_0 \quad \varepsilon_B = -\varepsilon_0 \quad (13)$$

and introduce the variables

$$x_0 = \frac{\varepsilon_0}{2V}, \quad x_c = \frac{\varepsilon_c(z)}{2V}, \quad \omega = \frac{z}{2V}. \quad (14)$$

Eq. (11) can then be written as

$$x_c = (2c - 1)x_0 + \frac{x_0^2 - x_c^2}{\sqrt{(\omega - x_c)^2 - 1}}. \quad (15)$$

Solve this equation numerically by writing a corresponding computer code!

(a) An iterative solution can start with $x_c^{(1)} = (2c - 1)x_0$ (in fact, this is the virtual crystal approximation). Apply a small positive imaginary part for ω ($\text{Im } \omega \simeq 0.01 - 0.05$) and use a linear mixing scheme,

$$x_c^{(n+1),in} = \alpha x_c^{(n),out} + (1 - \alpha) x_c^{(n),in} \quad (16)$$

with a suitable value of α ($\alpha \simeq 0.1 - 0.5$)!

Important note: from the two possible values of $\sqrt{(\omega - x_c)^2 - 1}$ the one with negative imaginary part should be chosen!

(b) More preferably, the well-coverging iterative process proposed in the course should be used. Start again with $x_c^{(0)} = (2c - 1)x_0$, then follow the steps:

$$1: \quad G_c^{00(n)}(z) = \frac{1}{\sqrt{(\omega - x_c^{(n)})^2 - 1}} \quad (17)$$

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$$2: \quad t_c^{(n)} = \frac{c(x_0 - x_c^{(n)})}{1 - (x_0 - x_c^{(n)})G_c^{00(n)}} - \frac{(1 - c)(x_0 + x_c^{(n)})}{1 + (x_0 + x_c^{(n)})G_c^{00(n)}} \quad (18)$$

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$$3: \quad x_c^{(n+1)} = x_c^{(n)} + \frac{t_c^{(n)}}{1 + t_c^{(n)}G_c^{00(n)}} \quad (19)$$

$$\text{repeat from step 1 until convergence} \quad (20)$$

After getting the self-consistent solution for x_c , plot the dimensionless averaged density of states,

$$n_c(\omega) = -\text{Im} \frac{1}{\sqrt{(\omega - x_c)^2 - 1}}, \quad (21)$$

for (i) $c = 0.5$ and $x_0 = 1$, (ii) for $c = 0.5$ and $x_0 = 2$, and (iii) for $c = 0.1$ and $x_0 = 2$!